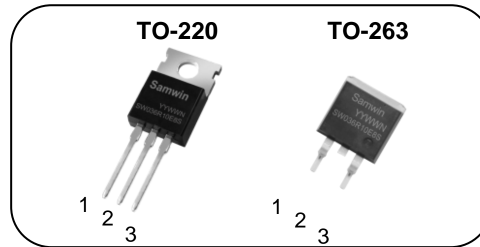
N-channel Enhanced mode TO-220/TO-263 MOSFET

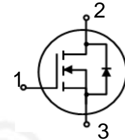
Features

- High ruggedness
- Low $R_{DS(ON)}$ (Typ 3.8mΩ)@V_{GS}=10V
- Low Gate Charge (Typ 85nC)
- Improved dv/dt Capability
- 100% Avalanche Tested
- Application:Synchronous Rectification, Li Battery Protect Board, Motor Drivers



1. Gate 2.Drain 3.Source

BV_{DSS} : 100V
I_D : 175A
$R_{DS(ON)}$:3.8mΩ



General Description

This power MOSFET is produced with advanced technology of SAMWIN.
This technology enable the power MOSFET to have better characteristics, including fast switching time, low on resistance, low gate charge and especially excellent avalanche characteristics.

Order Codes

Item	Sales Type	Marking	Package	Packaging
1	SW P 036R10E8S	SW036R10E8S	TO-220	TUBE
2	SW B 036R10E8S	SW036R10E8S	TO-263	TUBE

Absolute maximum ratings

Symbol	Parameter		Value		Unit
			TO-220	TO-263	
V_{DSS}	Drain to source voltage		100		V
I_D	Continuous drain current (@T_C=25ºC,Silicon Limited)		175*		A
	Continuous drain current (@T_C=100ºC,Silicon Limited)		132*		A
	Continuous drain current (@T_C=25ºC,Package Limited)		135		A
I_{DM}	Drain current pulsed	(note 1)	700		A
V_{GS}	Gate to source voltage		±20		V
E_{AS}	Single pulsed avalanche energy	(note 2)	812		mJ
E_{AR}	Repetitive avalanche energy	(note 1)	80		mJ
dv/dt	Peak diode recovery dv/dt	(note 3)	5		V/ns
P_D	Total power dissipation (@T_C=25ºC)		312.5		W
	Derating factor above 25ºC		2.5		W/ºC
T_{STG}, T_J	Operating junction temperature & storage temperature		-55 ~ + 150		ºC
T_L	Maximum lead temperature for soldering purpose, 1/8 from case for 5 seconds.		300		ºC

*. Drain current is limited by junction temperature. Package limitation current is 135A.

Thermal characteristics

Symbol	Parameter	Value		Unit
		TO-220	TO-263	
R_{thjc}	Thermal resistance, Junction to case	0.4		ºC/W
R_{thja}	Thermal resistance, Junction to ambient	53		ºC/W

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Electrical characteristic (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
Off characteristics						
BV_{DSS}	Drain to source breakdown voltage	V_{GS}=0V, I_D=250uA	100			V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown voltage temperature coefficient	I_D=250uA, referenced to 25°C		0.05		V/°C
I_{DSS}	Drain to source leakage current	V_{DS}=100V, V_{GS}=0V			1	uA
		V_{DS}=80V, T_J=125°C			50	uA
I_{GSS}	Gate to source leakage current, forward	V_{GS}=20V, V_{DS}=0V			100	nA
	Gate to source leakage current, reverse	V_{GS}=-20V, V_{DS}=0V			-100	nA
On characteristics						
$V_{GS(TH)}$	Gate threshold voltage	V_{DS}=V_{GS}, I_D=250uA	2		4	V
$R_{DS(ON)}$	Drain to source on state resistance	V_{GS}=10V, I_D=20A, T_J=25°C		3.8	4.6	mΩ
		V_{GS}=10V, I_D=20A, T_J=125°C		6.2		mΩ
G_{fs}	Forward transconductance	V_{DS}=5V, I_D=30A		76		S
Dynamic characteristics						
C_{iss}	Input capacitance	V_{GS}=0V, V_{DS}=50V, f=100kHz		6263		pF
C_{oss}	Output capacitance			939		
C_{rss}	Reverse transfer capacitance			19		
$t_{d(on)}$	Turn on delay time	V_{DS}=50V, I_D=30A, R_G=4.7Ω, V_{GS}=10V (note 4,5)		33		ns
t_r	Rising time			35		
$t_{d(off)}$	Turn off delay time			59		
t_f	Fall time			14		
Q_g	Total gate charge	V_{DS}=80V, V_{GS}=10V, I_D=30A, I_G=5mA (note 4,5)		85		nC
Q_{gs}	Gate-source charge			31		
Q_{gd}	Gate-drain charge			13		
R_g	Gate resistance	V_{DS}=0V, Scan F mode		3		Ω

Source to drain diode ratings characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_S	Continuous source current	Integral reverse p-n Junction diode in the MOSFET			175	A
I_{SM}	Pulsed source current				700	A
V_{SD}	Diode forward voltage drop.	I_S=50A, V_{GS}=0V			1.4	V
t_{rr}	Reverse recovery time	I_S=30A, V_{GS}=0V, dI_F/dt=100A/us		68		ns
Q_{rr}	Reverse recovery charge			142		nC

※. Notes

1. Repeatitive rating : pulse width limited by junction temperature.
2. L =0.5mH, I_{AS} =57A, V_{DD}=50V, R_G=25Ω, Starting T_J = 25°C
3. I_{SD} ≤30A, di/dt = 100A/us, V_{DD} ≤ BV_{DSS}, Staring T_J =25°C
4. Pulse Test : Pulse Width ≤ 300us, duty cycle ≤ 2%.
5. Essentially independent of operating temperature.

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Fig. 1. On-state characteristics

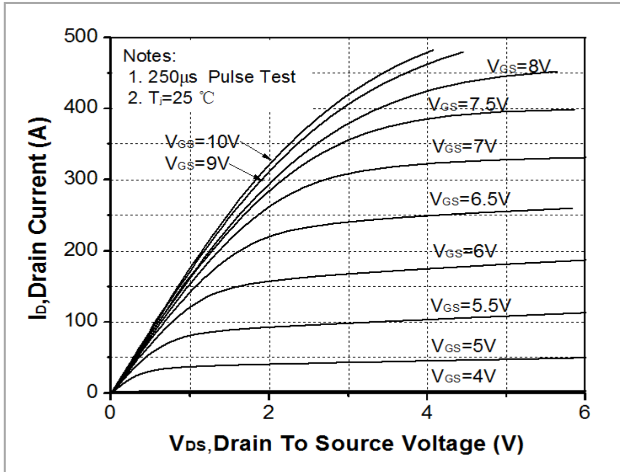

Fig. 2. Transfer Characteristics

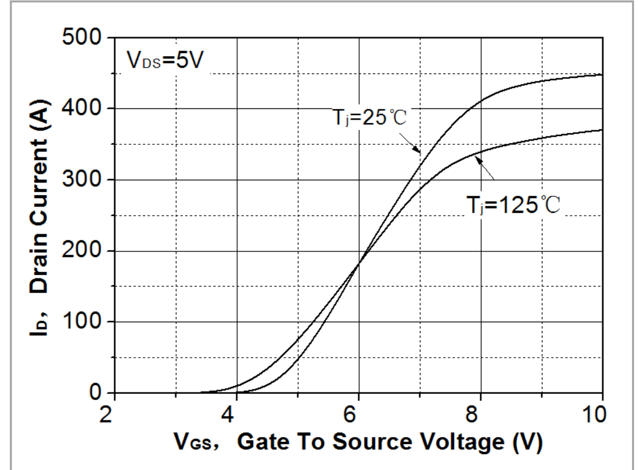

Fig. 3. On-resistance variation vs. drain current and gate voltage

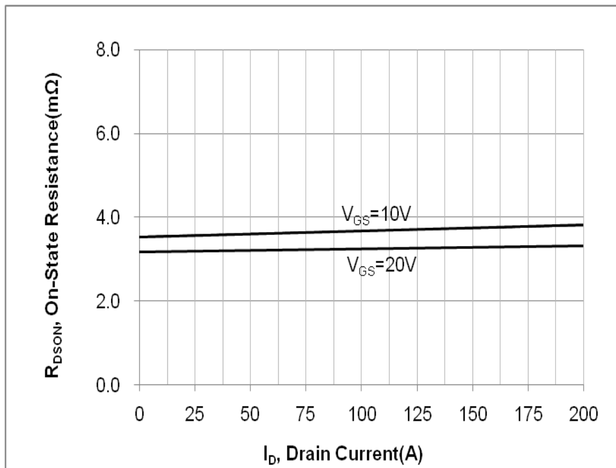

Fig. 4. On-state current vs. diode forward voltage

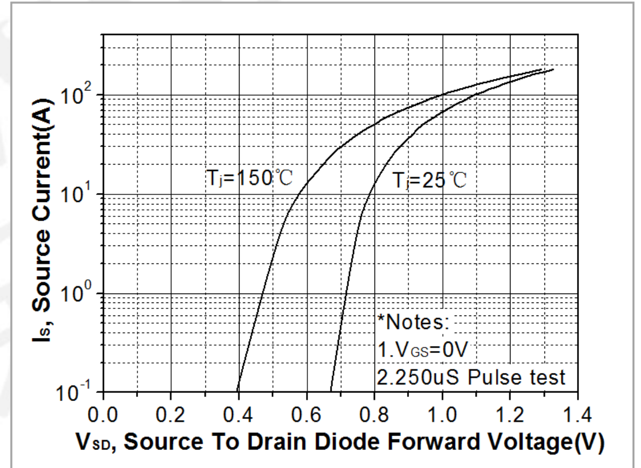

Fig 5. Breakdown voltage variation vs. junction temperature

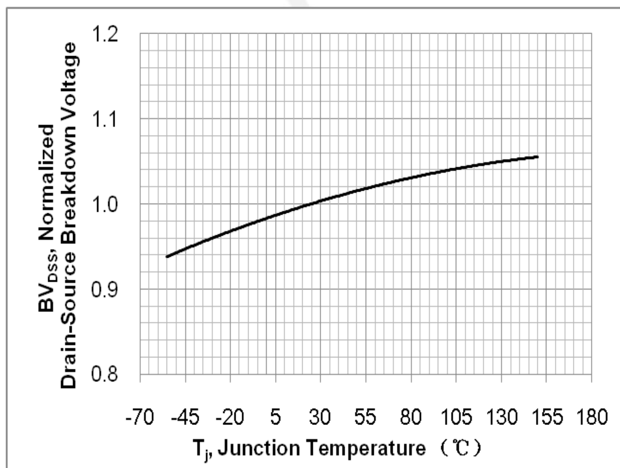

Fig. 6. On-resistance variation vs. junction temperature

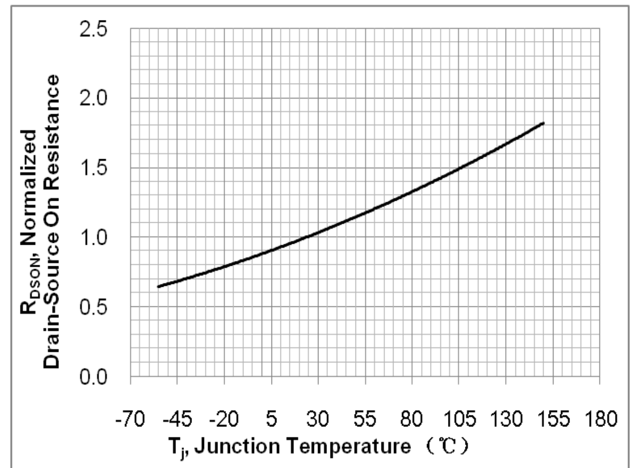

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Fig. 7. Gate charge characteristics

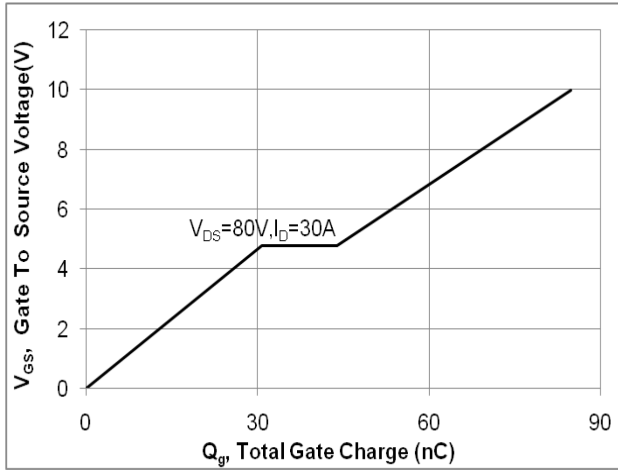

Fig. 8. Capacitance Characteristics

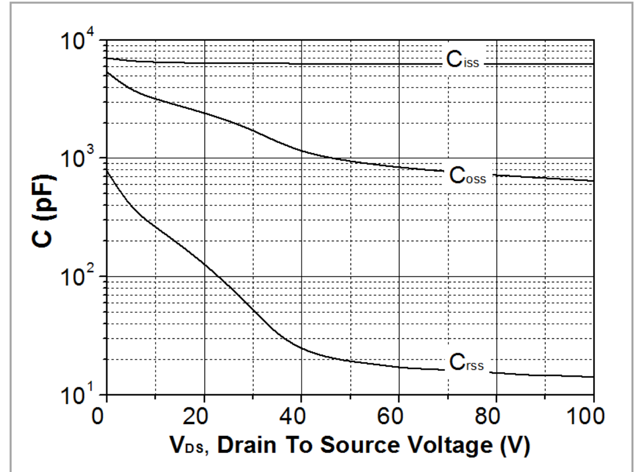

Fig. 9. Maximum safe operating area (TO-220/TO-263)

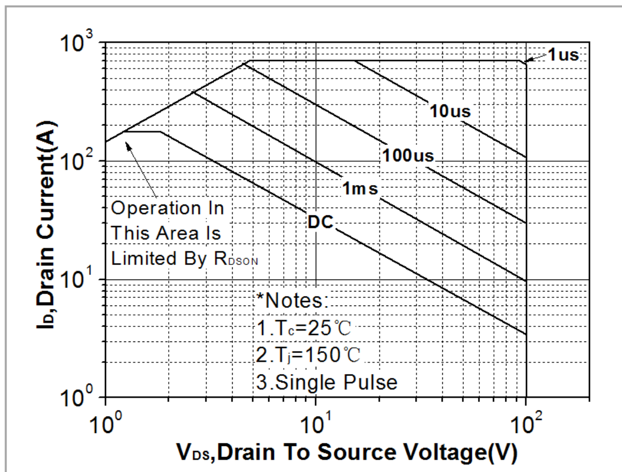

Fig. 10. Maximum drain current vs. case temperature(TO-220/TO-263)

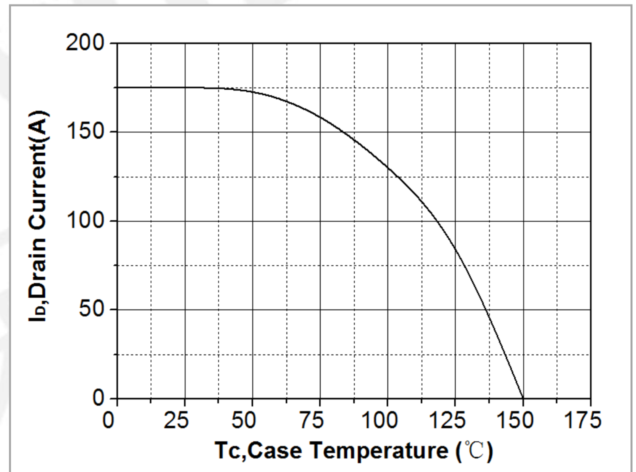

Fig. 11. Transient thermal response curve(TO-220/TO-263)

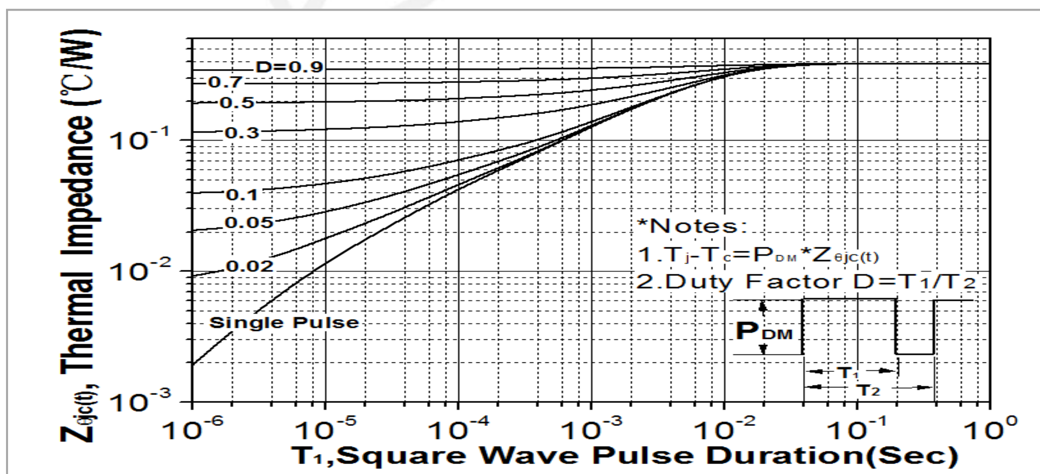

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Fig. 12. Gate charge test circuit & waveform

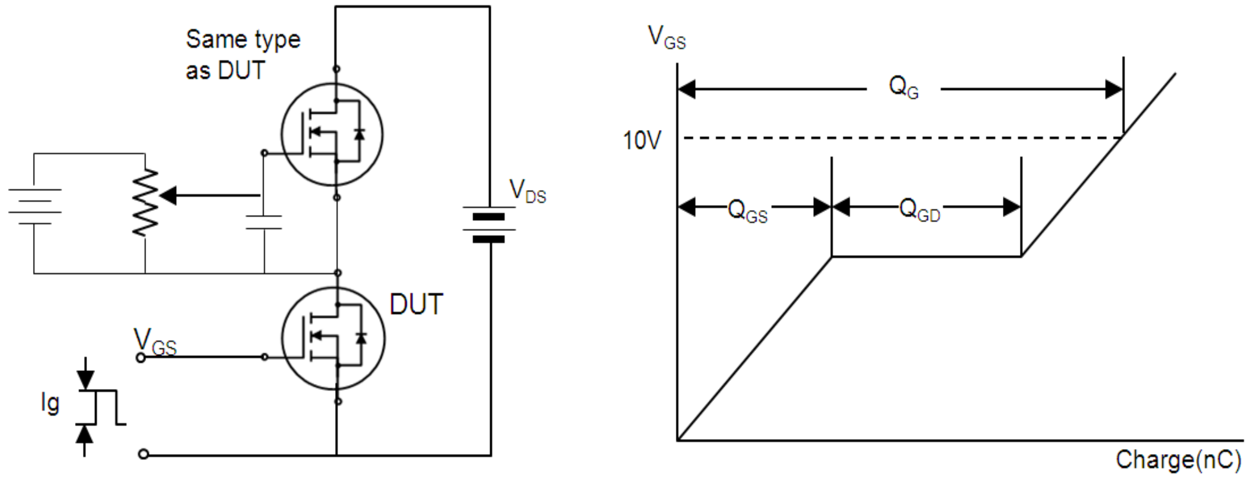

Fig. 13. Switching time test circuit & waveform

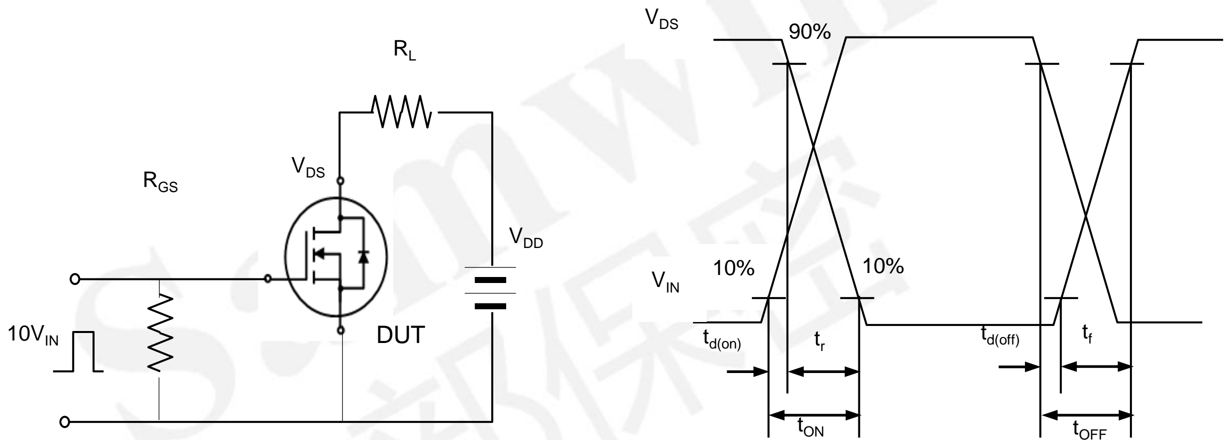

Fig. 14. Unclamped Inductive switching test circuit & waveform

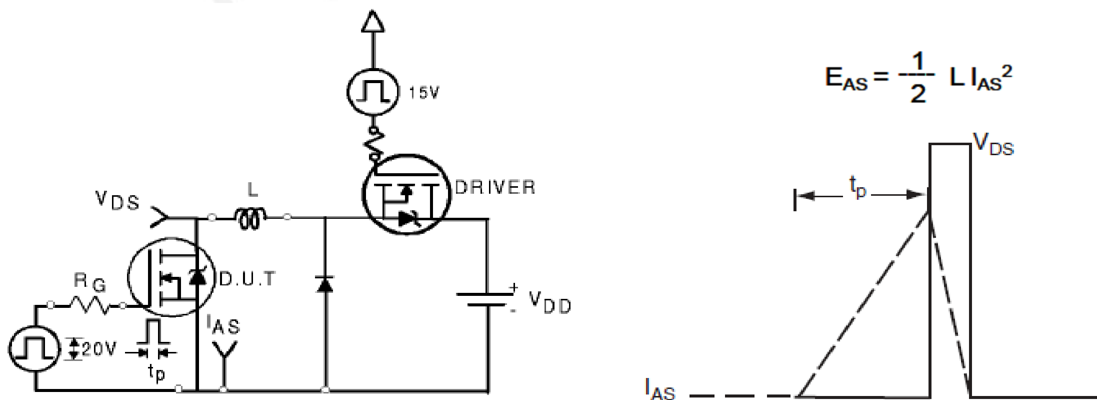

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Fig. 15. Peak diode recovery dv/dt test circuit & waveform

DUT
+ V_{DS}
-
I_S
L
V_{DS}
R_G
V_{DD}
$10V_{GS}$
Same type
as DUT

*. dv/dt controlled by RG
*. Is controlled by pulse period

V_{GS} (DRIVER)
10V
I_S (DUT)
di/dt
I_{RRM}
Diode reverse current
Diode recovery dv/dt
V_{DS} (DUT)
V_F
V_{DD}
Body diode forward voltage drop

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DISCLAIMER

* All the data & curve in this document was tested in SEMIPOWER TESTING & APPLICATION CENTER.
* This product has passed the PCT,TC,HTRB,HTGB,HAST,PC and Solderdunk reliability testing.
* Qualification standards can also be found on the Web site (**http://www.semipower.com.cn**)
* Suggestions for improvement are appreciated, Please send your suggestions to **samwin@samwinsemi.com**

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